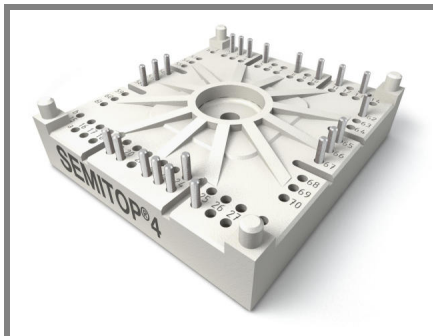


SK75GD066T



SEMITOP® 4

IGBT Module

SK75GD066T

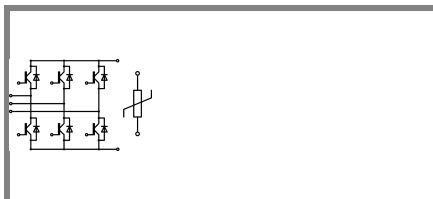
Preliminary Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

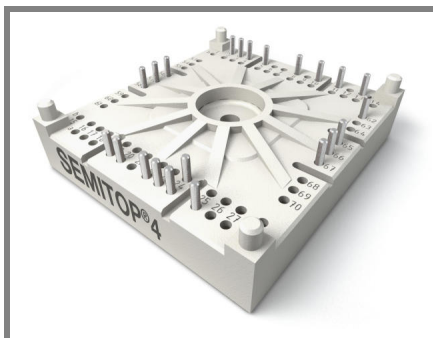
- Inverter up to 16 kVA
- Typ. motor power 7,5 kW



GD-T

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}	$T_j = 25\text{ °C}$	600	V
I_C	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	83 A
		$T_s = 70\text{ °C}$	67 A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	150	A
V_{GES}		± 20	V
t_{psc}	$V_{CC} = 360\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 125\text{ °C}$ $V_{CES} < 600\text{ V}$	6	μs
Inverse Diode			
I_F	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	92 A
		$T_s = 70\text{ °C}$	73 A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	150	A
Module			
$I_{t(RMS)}$			A
T_{vj}		-40 ... +175	$^{\circ}\text{C}$
T_{stg}		-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 1,2\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$		0,0038	mA
		$T_j = 125\text{ °C}$			mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$	$T_j = 25\text{ °C}$		600	nA
		$T_j = 125\text{ °C}$			nA
V_{CE0}		$T_j = 25\text{ °C}$	0,8	1,1	V
		$T_j = 150\text{ °C}$	0,7	1	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	8	10	$\text{m}\Omega$
		$T_j = 150\text{ °C}$	12,7	14	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 75\text{ A}$, $V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	1,45	1,85	V
		$T_j = 150\text{ °C}_{chiplev.}$	1,65	2,05	V
C_{ies}	$V_{CE} = 25$, $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	4,7		nF
C_{oes}			0,3		nF
C_{res}			0,145		nF
$t_{d(on)}$	$R_{Gon} = 16\ \Omega$ $di/dt = 2250\text{ A}/\mu\text{s}$	$V_{CC} = 300\text{ V}$ $I_C = 75\text{ A}$	95		ns
t_r			50		ns
E_{on}	$R_{Goff} = 16\ \Omega$ $di/dt = 2250\text{ A}/\mu\text{s}$	$T_j = 150\text{ °C}$ $V_{GE} = -7/+15\text{ V}$	3,1		mJ
$t_{d(off)}$			541		ns
t_f			70		ns
E_{off}			2,8		mJ
$R_{th(j-s)}$	per IGBT		0,75		K/W



SEMITOP® 4

IGBT Module

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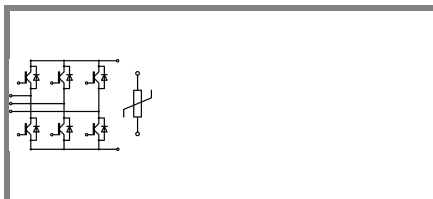
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- Inverter up to 16 kVA
- Typ. motor power 7,5 kW



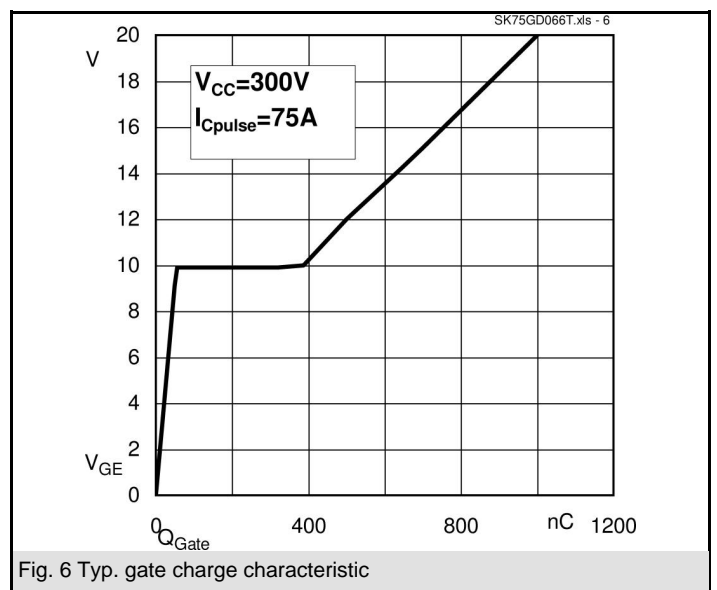
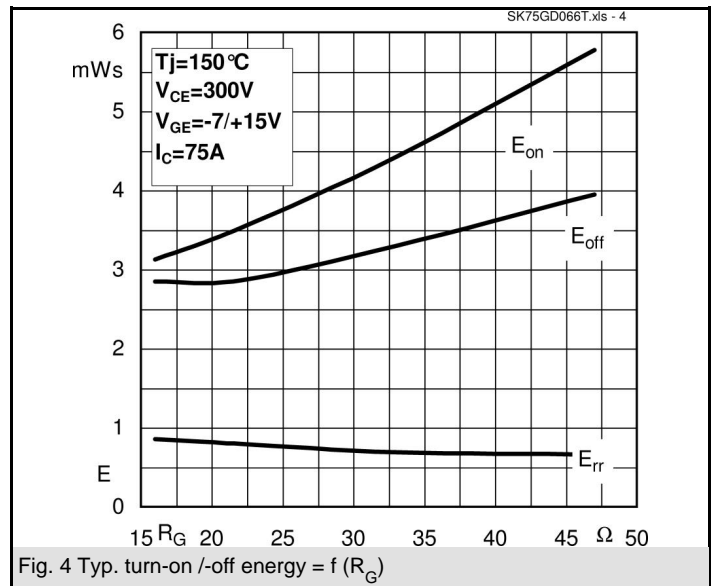
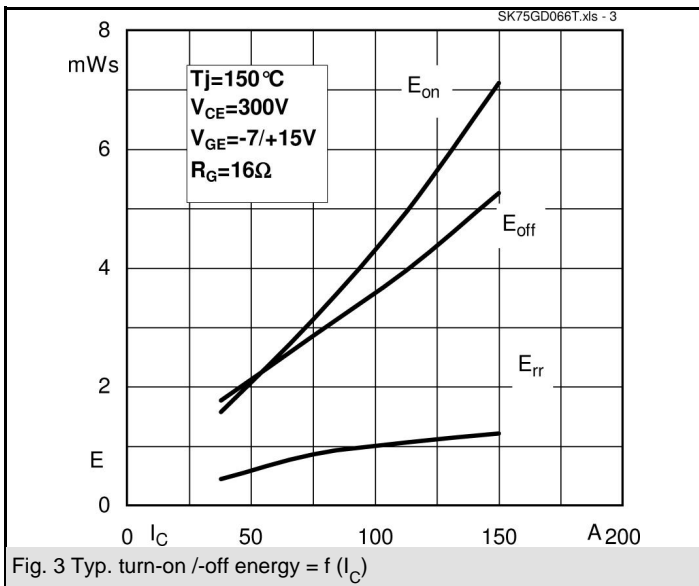
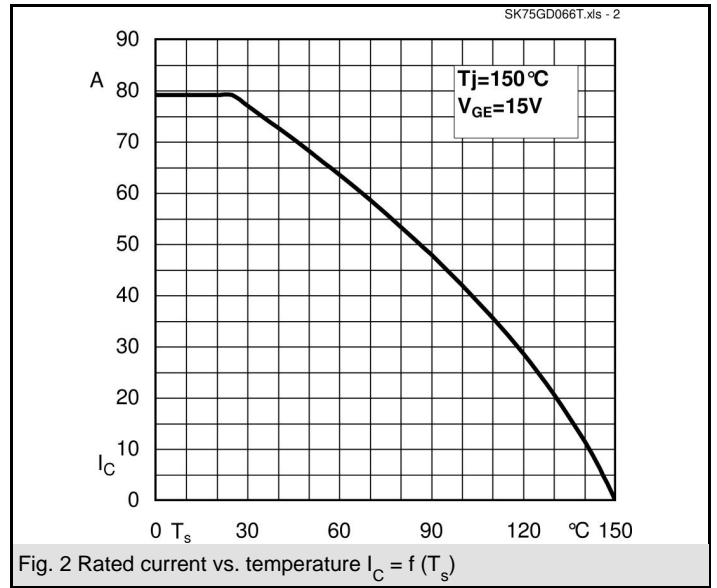
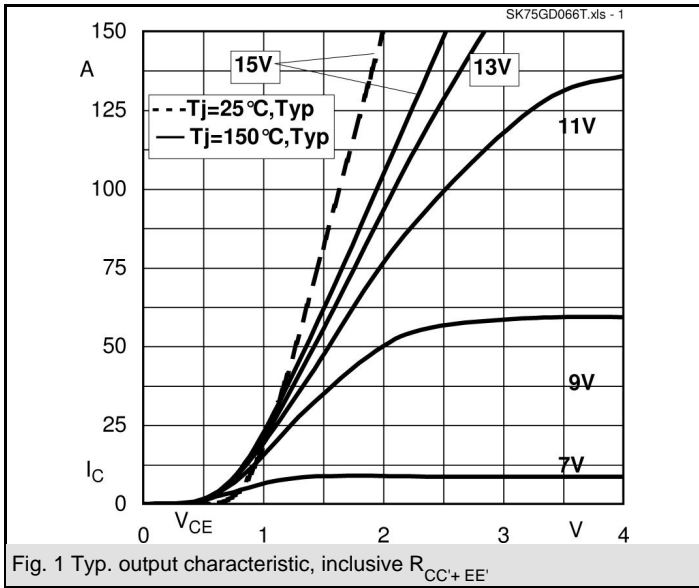
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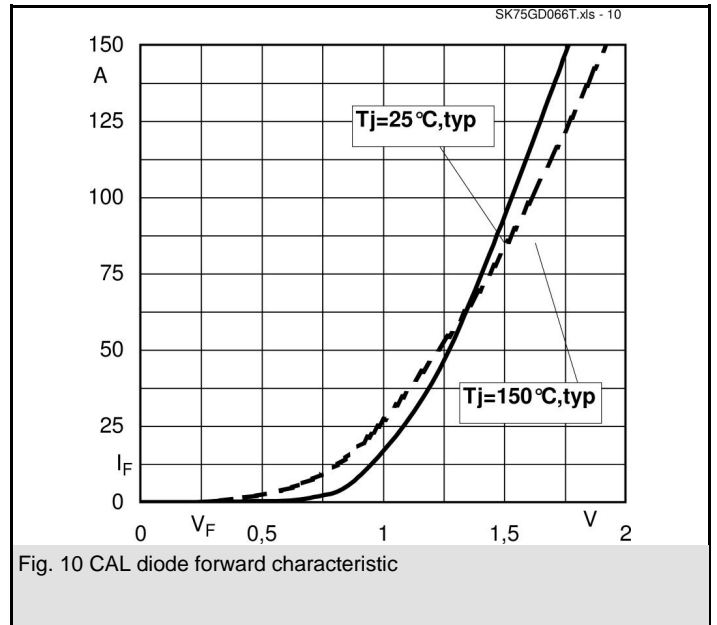
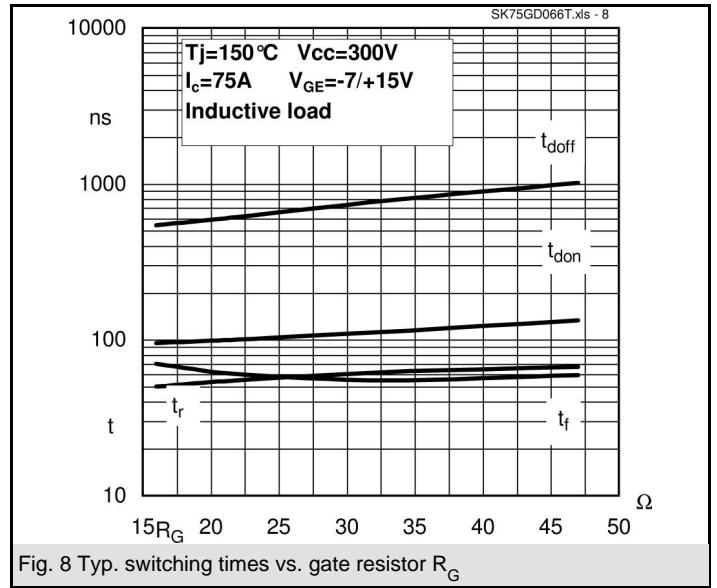
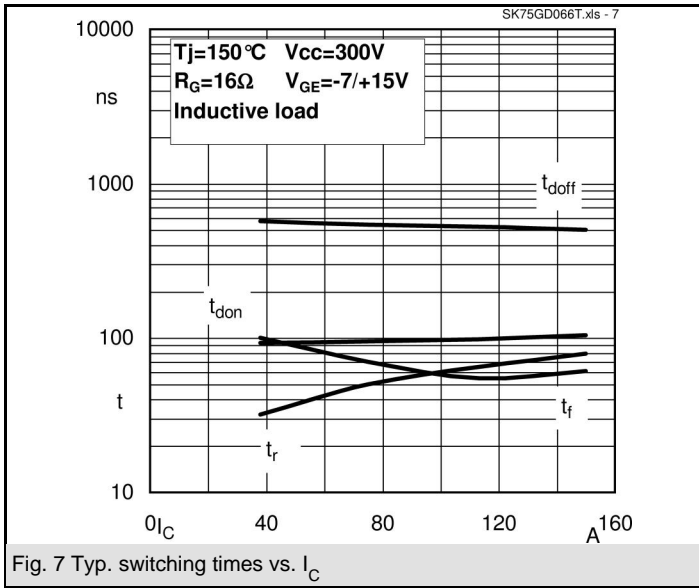
Characteristics

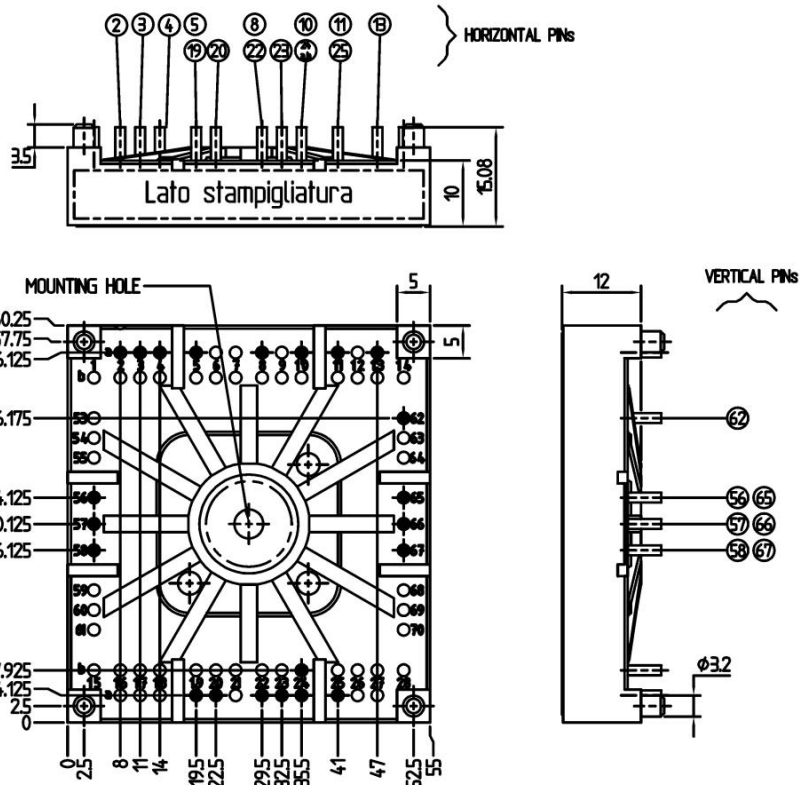
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 60 \text{ A}; V_{GE} = 0 \text{ V}$		$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	1,35	V
			$T_j = 150 \text{ }^\circ\text{C}_{chiplev.}$	1,31	V
V_{F0}			$T_j = 25 \text{ }^\circ\text{C}$		V
			$T_j = 150 \text{ }^\circ\text{C}$	0,85	V
r_F			$T_j = 25 \text{ }^\circ\text{C}$		mΩ
			$T_j = 150 \text{ }^\circ\text{C}$	7,8	mΩ
I_{RRM}	$I_F = 75 \text{ A}$	$T_j = 150 \text{ }^\circ\text{C}$	60		A
Q_{rr}	$di/dt = 2250 \text{ A}/\mu\text{s}$		6		μC
E_{rr}	$V_{CC} = 300\text{V}$		0,85		mJ
$R_{th(j-s)D}$	per diode		1,2		K/W
M_s	to heat sink	2,5		2,75	Nm
w			60		g
Temperature sensor					
R_{100}	$T_s = 100^\circ\text{C} (R_{25}=5\text{k}\Omega)$		493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

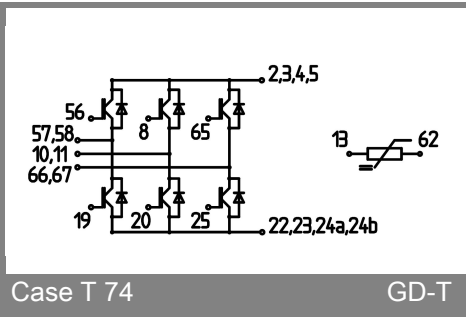
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Case T74 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



Case T 74

GD-T

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